DD100GB has two diode chips connected in series and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 800V is avaiable for various input voltage. Isolated mounting

- •Two elements i connections
- Highly reliable gla

DIODE MODULE

• High surge curre



SanRex

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ng base in a package for simple (single and three phase) bridge	
lass passivated chips ent capability	<u>_16.5</u> <u>23</u>

DD

-02

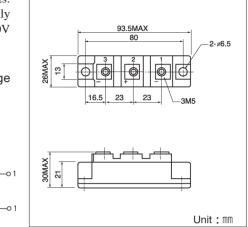
2 Q

KD

(Applications)

Various rectifiers, Battery chargers, DC motor drives

DD(KD)100GB40/80 Power Diode Module DD100GB series are designed for various rectifier circuits.



TOP

Maximum Ratings

Maximum Ratings				
Symbol	Item	Ratings		Unit
	item	DD100GB40	DD100GB80	Unit
VRRM	Repetitive Peak Reverse Voltage	400	800	V
VRSM	Non-Repetitive Peak Reverse Voltage	480	960	V

Symbol	Item		Conditions	Ratings	Unit
IF (AV)	Average Forward Current		Single phase, half wave, 180° conduction, Tc: 115°C	100	Α
F (RMS)	R.M.S. Forward Current		Single phase, half wave, 180° conduction, Tc: 115°C	155	Α
IFSM	Surge Forward Current		¹ / ₂ cycle, 50/60Hz, peak value, non-repetitive	1800/2000	Α
l²t	l²t		Value for one cycle of surge current	16500	A ² S
Tj	Junction Temperature			-40~+150	°C
Tstg	Storage Temperature			-40~+125	°C
Viso	Isolation Breakdown Voltage (R.M.S.)		A.C.1minute	2500	V
	Mounting	Mounting (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	N∙m
	Torque	Terminal (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	(kgf•cm)
	Mass			170	g

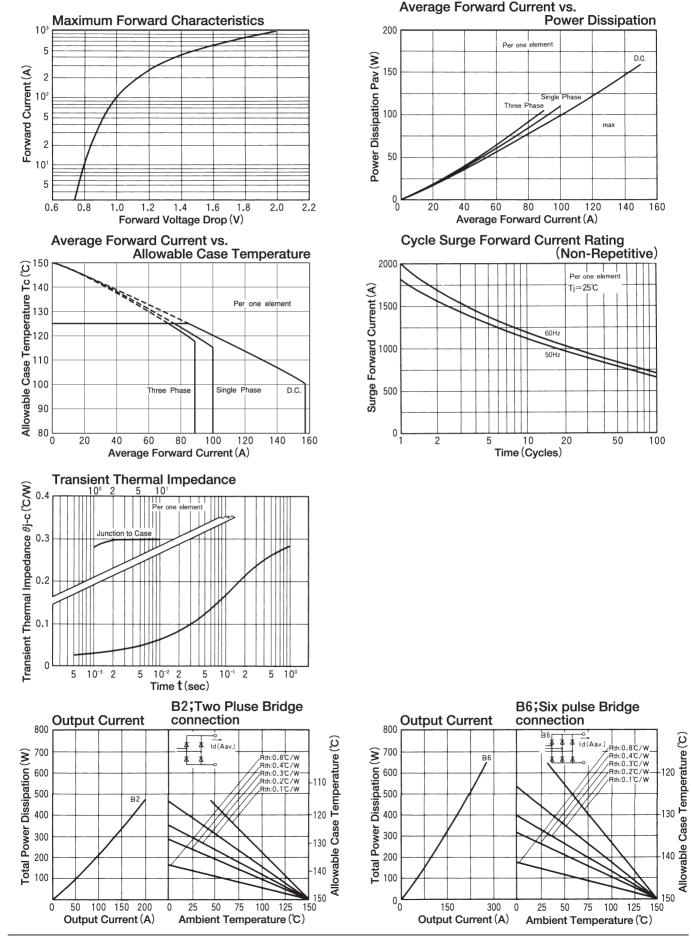
Electrical Characteristics

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Symbol	Item	n Conditions		Unit
Irrm	Repetitive Peak Reverse Current, max.	at VDRM, single phase, half wave. Tj=150 ℃	30	mA
Vfm	Forward Voltage Drop, max.	Foward current 320A, Tj=25°C, Inst. measurement	1.25	V
Rth (j-c)	Thermal Impedance, max.	Junction to case	0.30	°C\W







SANSHA ELECTRIC